

SGP10N60RUFD

600 V, 10 A Short Circuit Rated IGBT

General Description

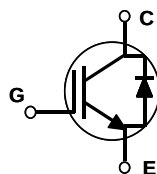
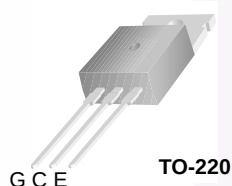
Fairchild's RUFD series of Insulated Gate Bipolar Transistors (IGBTs) provide low conduction and switching losses as well as short circuit ruggedness. The RUFD series is designed for applications such as motor control, Uninterrupted Power Supplies (UPS) and general inverters where short circuit ruggedness is a required feature.

Features

- 10 A, 600 V, $T_C = 100^\circ\text{C}$
- Low Saturation Voltage: $V_{CE(sat)} = 2.1\text{ V @ } I_C = 10\text{ A}$
- Typical Fall Time. 242ns at $T_J = 125^\circ\text{C}$
- High Speed Switching
- High Input Impedance
- Short Circuit Rating

Applications

Motor Control, UPS, General Inverter



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	Ratings	Unit
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	16	A
	Collector Current @ $T_C = 100^\circ\text{C}$	10	A
$I_{CM(1)}$	Pulsed Collector Current	30	A
I_F	Diode Continuous Forward Current @ $T_C = 25^\circ\text{C}$	24	A
	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	12	A
I_{FM}	Diode Maximum Forward Current	92	A
T_{SC}	Short Circuit Withstand Time @ $T_C = 100^\circ\text{C}$	10	us
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	75	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	30	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction-to-Case	--	1.6	$^\circ\text{C/W}$
$R_{\theta JC}(\text{DIODE})$	Thermal Resistance, Junction-to-Case	--	2.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C/W}$

Electrical Characteristics of the IGBT $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	600	--	--	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	--	0.6	--	V/°C
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	--	--	250	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	--	--	± 100	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 10\text{ mA}, V_{CE} = V_{GE}$	5.0	6.0	8.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 10\text{ A}, V_{GE} = 15\text{ V}$	--	2.2	2.8	V
		$I_C = 16\text{ A}, V_{GE} = 15\text{ V}$	--	2.5	--	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V},$ $f = 1\text{ MHz}$	--	660	--	pF
C_{oes}	Output Capacitance		--	115	--	pF
C_{res}	Reverse Transfer Capacitance		--	25	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300\text{ V}, I_C = 10\text{ A},$ $R_G = 20\text{ }\Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 25^\circ\text{C}$	--	15	--	ns
t_r	Rise Time		--	30	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	36	50	ns
t_f	Fall Time		--	158	200	ns
E_{on}	Turn-On Switching Loss		--	141	--	μJ
E_{off}	Turn-Off Switching Loss	$V_{CC} = 300\text{ V}, I_C = 10\text{ A},$ $R_G = 20\text{ }\Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 125^\circ\text{C}$	--	215	--	μJ
E_{ts}	Total Switching Loss		--	356	500	μJ
$t_{d(on)}$	Turn-On Delay Time		--	16	--	ns
t_r	Rise Time		--	33	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	42	60	ns
t_f	Fall Time		--	242	350	ns
E_{on}	Turn-On Switching Loss		--	161	--	μJ
E_{off}	Turn-Off Switching Loss		--	452	--	μJ
E_{ts}	Total Switching Loss		--	613	860	μJ
T_{sc}	Short Circuit Withstand Time	$V_{CC} = 300\text{ V}, V_{GE} = 15\text{ V}$ @ $T_C = 100^\circ\text{C}$	10	--	--	μs
Q_g	Total Gate Charge	$V_{CE} = 300\text{ V}, I_C = 10\text{ A},$ $V_{GE} = 15\text{ V}$	--	30	45	nC
Q_{ge}	Gate-Emitter Charge		--	5	10	nC
Q_{gc}	Gate-Collector Charge		--	8	16	nC
L_e	Internal Emitter Inductance	Measured 5mm from PKG	--	7.5	--	nH

Electrical Characteristics of DIODE $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
V _{FM}	Diode Forward Voltage	I _F = 12 A	T _C = 25°C	--	1.4	1.7	V
			T _C = 100°C	--	1.3	--	
t _{rr}	Diode Reverse Recovery Time	I _F = 12 A, di _F /dt=200 A/μs	T _C = 25°C	--	42	60	ns
			T _C = 100°C	--	60	--	
I _{rr}	Diode Peak Reverse Recovery Current		T _C = 25°C	--	3.5	6.0	A
			T _C = 100°C	--	5.6	--	
Q _{rr}	Diode Reverse Recovery Charge		T _C = 25°C	--	80	180	nC
			T _C = 100°C	--	220	--	

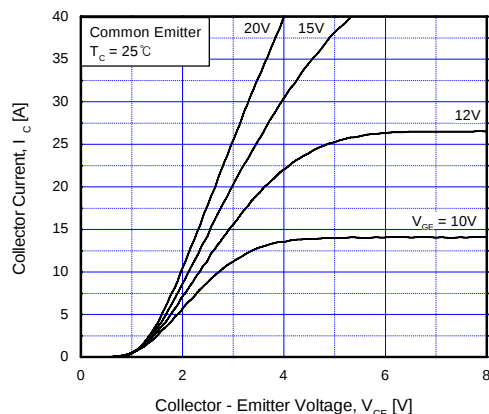


Fig 1. Typical Output Characteristics

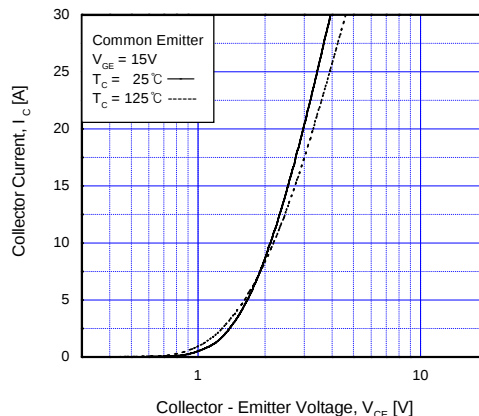


Fig 2. Typical Saturation Voltage Characteristics

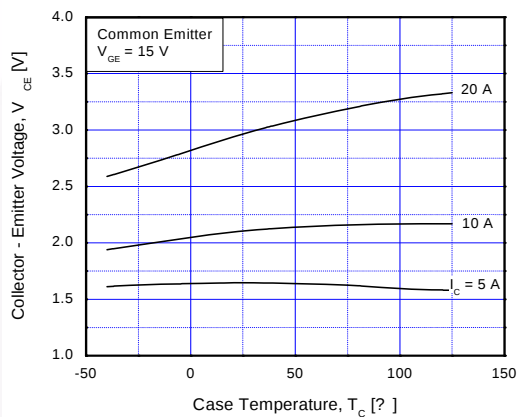


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

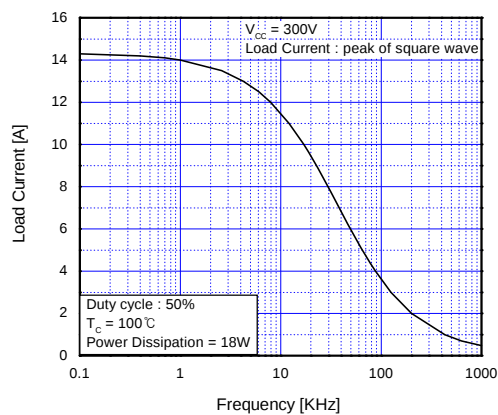
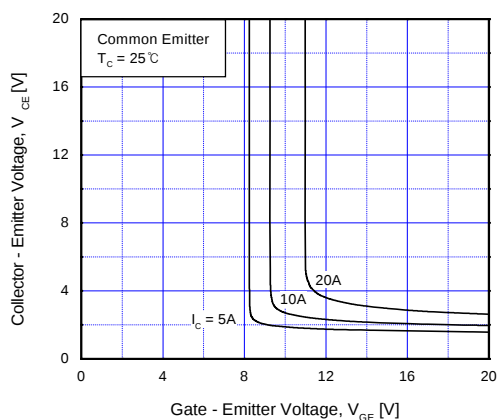
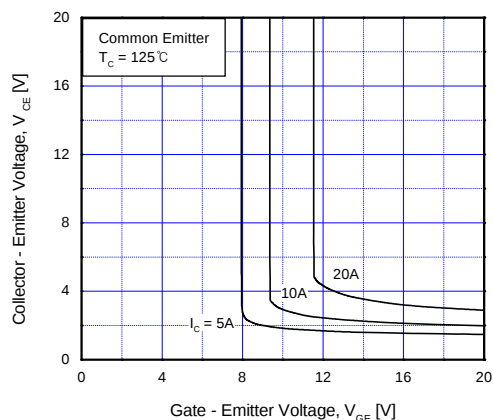


Fig 4. Load Current vs. Frequency

Fig 5. Saturation Voltage vs. V_{GE} Fig 6. Saturation Voltage vs. V_{GE}

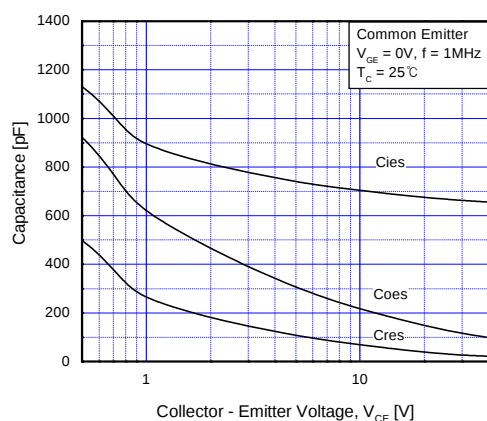


Fig 7. Capacitance Characteristics

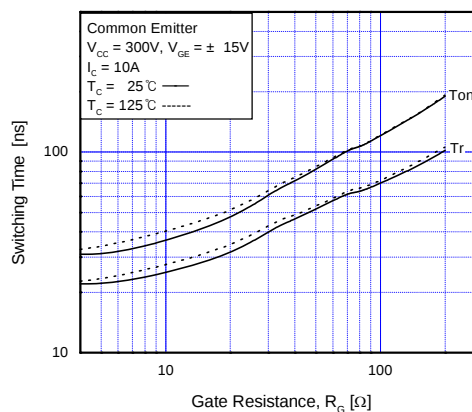


Fig 8. Turn-On Characteristics vs. Gate Resistance

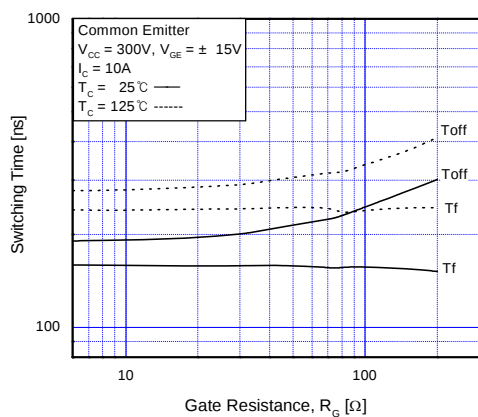


Fig 9. Turn-Off Characteristics vs. Gate Resistance

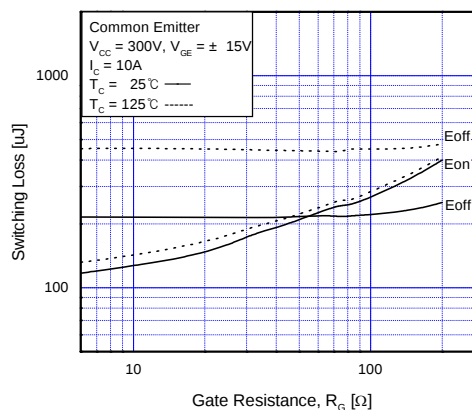


Fig 10. Switching Loss vs. Gate Resistance

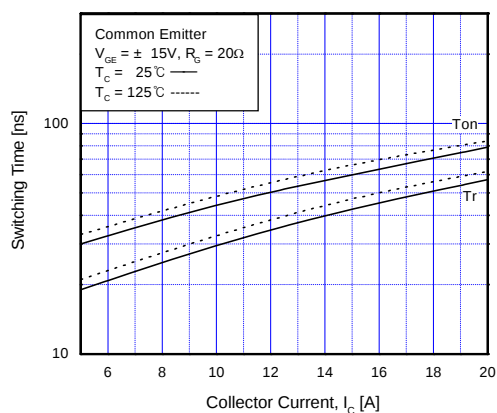


Fig 11. Turn-On Characteristics vs. Collector Current

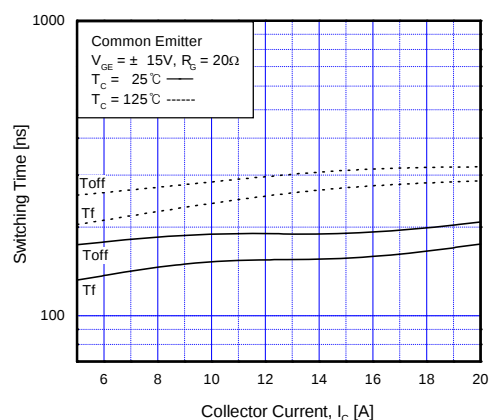


Fig 12. Turn-Off Characteristics vs. Collector Current

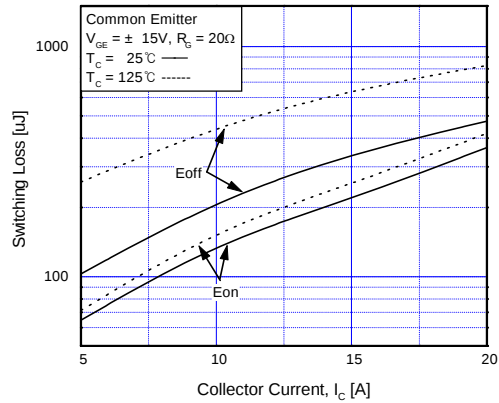


Fig 13. Switching Loss vs. Collector Current

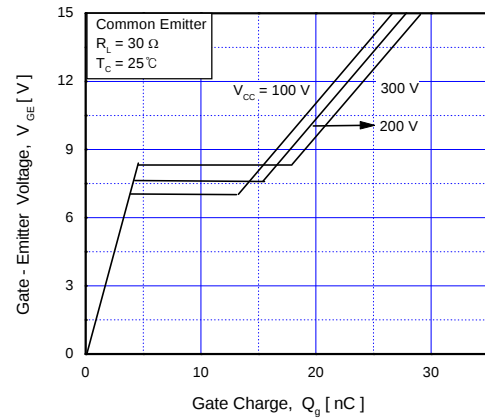


Fig 14. Gate Charge Characteristics

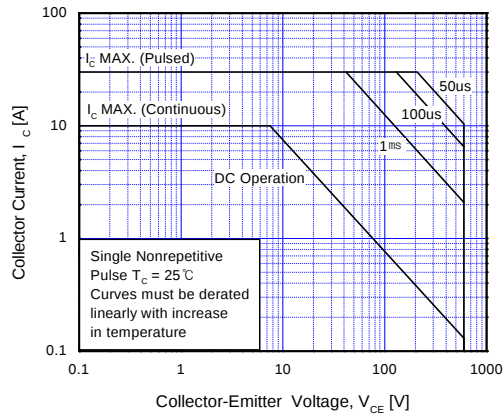


Fig 15. SOA Characteristics

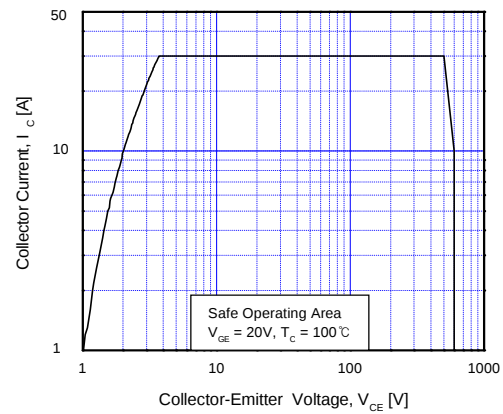


Fig 16. Turn-Off SOA Characteristics

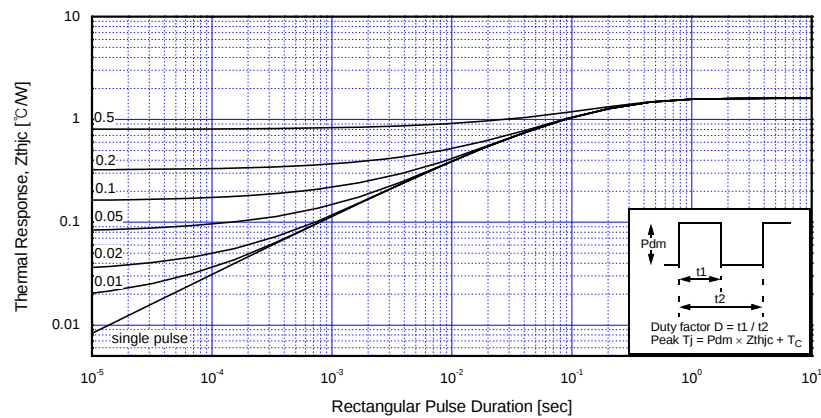


Fig 17. Transient Thermal Impedance of IGBT

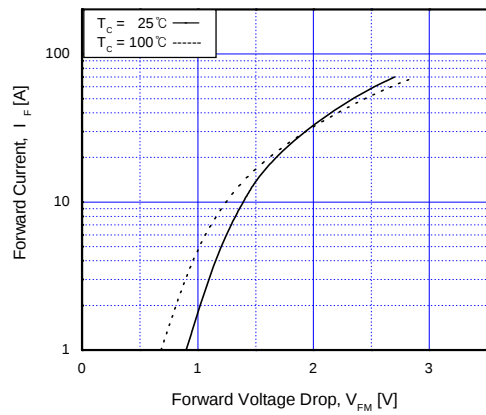


Fig 18. Forward Characteristics

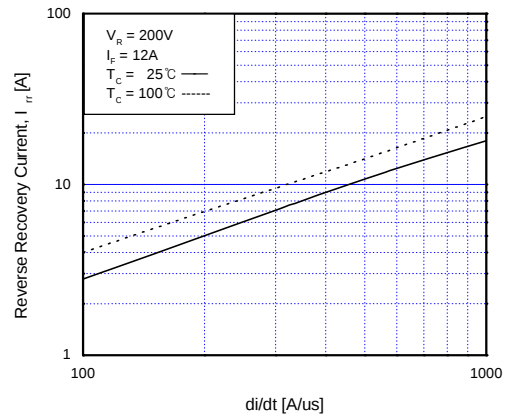


Fig 19. Reverse Recovery Current

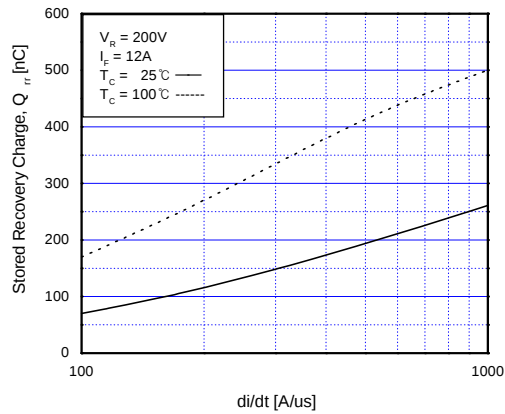


Fig 20. Stored Charge

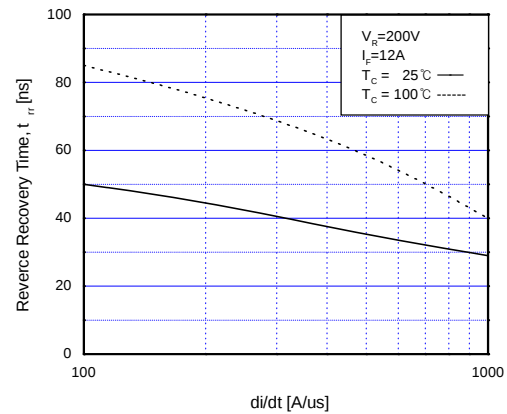


Fig 21. Reverse Recovery Time

Mechanical Dimensions

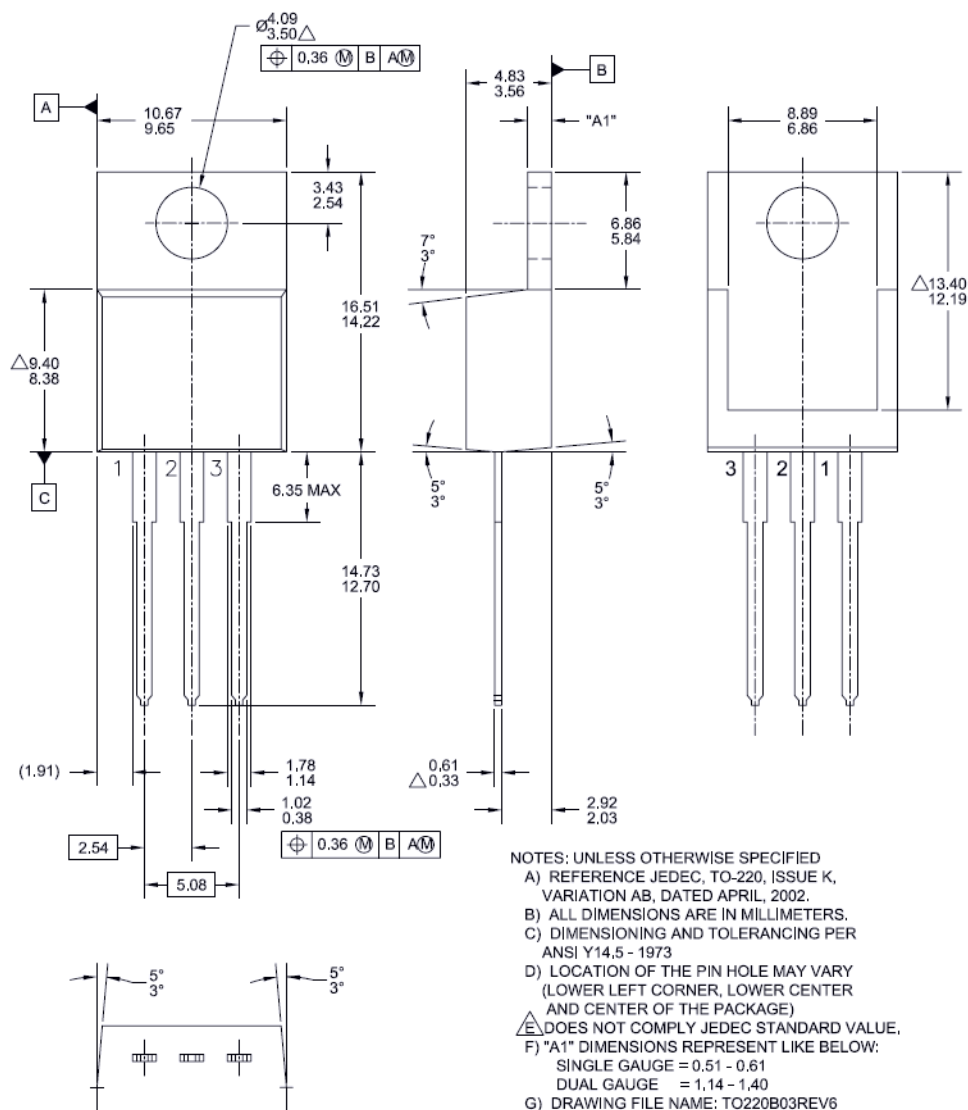


Figure 22. TO-220 3L - TO-220, MOLDED, 3LEAD, JEDEC VARIATION AB

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT220-003

